

## FEATURES

- $\pm 2$  V to  $\pm 6$  V dual-supply operation**
- 2 V to 12 V single-supply operation**
- Temperature range:  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$**
- <0.2 nA leakage currents**
- 52  $\Omega$  on resistance over full signal range**
- Rail-to-rail switching operation**
- 16-lead LFCSP and TSSOP packages**
- Typical power consumption: <0.1  $\mu\text{W}$**
- TTL-/CMOS-compatible inputs**
- Package upgrades to 74HC4053 and MAX4053/MAX4583**

## APPLICATIONS

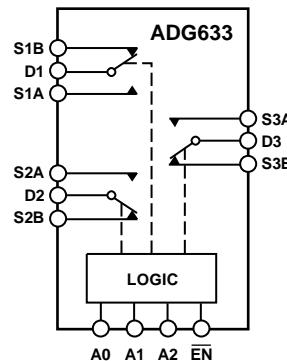
- Automatic test equipment**
- Data acquisition systems**
- Battery-powered systems**
- Communications systems**
- Audio and video signal routing**
- Relay replacement**
- Sample-and-hold systems**
- Industrial control systems**

## GENERAL DESCRIPTION

The **ADG633** is a low voltage CMOS device comprising three independently selectable single-pole, double-throw (SPDT) switches. The device is fully specified for  $\pm 5$  V, +5 V, and +3 V supplies. The **ADG633** switches are turned on with a logic low (or high) on the appropriate control input. Each switch conducts equally well in both directions when on and has an input signal range that extends to the supplies. An **EN** input is used to enable or disable the device. When the device is disabled, all channels are switched off.

The **ADG633** is designed on an enhanced process that provides lower power dissipation, yet is capable of high switching speeds. Low power consumption and an operating supply range of 2 V to 12 V make the **ADG633** ideal for battery-powered, portable instruments. All channels exhibit break-before-make switching action, preventing momentary shorting when switching channels.

## FUNCTIONAL BLOCK DIAGRAM



SWITCHES SHOWN FOR A LOGIC 1 INPUT.

03275-001

Figure 1.

All digital inputs have 0.8 V to 2.4 V logic thresholds, ensuring TTL/CMOS logic compatibility when using single +5 V or dual  $\pm 5$  V supplies.

The **ADG633** is available in a small, 16-lead TSSOP package and a 16-lead, 4 mm  $\times$  4 mm LFCSP package.

## PRODUCT HIGHLIGHTS

1. Single- and dual-supply operation. The **ADG633** offers high performance and is fully specified and guaranteed with  $\pm 5$  V, +5 V, and +3 V supply rails.
2. Temperature range:  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ .
3. Guaranteed break-before-make switching action.
4. Low power consumption, typically <0.1  $\mu\text{W}$ .
5. Small, 16-lead TSSOP and 16-lead, 4 mm  $\times$  4 mm LFCSP packages.

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## REVISION HISTORY

### 2/2017—Rev. A to Rev. B

Deleted B Version .....	Throughout
Changes to Features Section, Applications Section, and Product	
Highlights Section .....	1
Added Note 2 to Table 1; Renumbered Sequentially .....	3
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Changes to Figure 3 and Table 6.....	7
Updated Outline Dimensions .....	14
Changes to Ordering Guide .....	14

### 11/2009—Rev. 0 to Rev. A

Changes to Table 4.....	6
Added Table 5; Renumbered Sequentially .....	7
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Update Outline Dimensions .....	14
Changes to Ordering Guide .....	14

### 2/2003—Revision 0: Initial Version

## SPECIFICATIONS

### DUAL-SUPPLY OPERATION

$V_{DD} = +5$  V,  $V_{SS} = -5$  V, GND = 0 V,  $T_A = -40^\circ\text{C}$  to  $+125^\circ\text{C}$ , unless otherwise noted.

Table 1.

Parameter	+25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range				V	$V_{DD} = +4.5$ V, $V_{SS} = -4.5$ V
On Resistance, $R_{ON}$	52	90	100	$\Omega$ typ	$V_S = \pm 4.5$ V, $I_S = 1$ mA; see Figure 20
On-Resistance Match Between Channels, $\Delta R_{ON}$	0.8			$\Omega$ max	$V_S = \pm 4.5$ V, $I_S = 1$ mA; see Figure 20
On-Resistance Flatness, $R_{FLAT(ON)}$	1.3	1.8	2	$\Omega$ typ	$V_S = +3.5$ V, $I_S = 1$ mA
On-Resistance Flatness, $R_{FLAT(ON)}$	9			$\Omega$ max	$V_{DD} = +5$ V, $V_{SS} = -5$ V, $V_S = \pm 3$ V, $I_S = 1$ mA
On-Resistance Flatness, $R_{FLAT(ON)}$	12	13	14	$\Omega$ typ	$V_{DD} = +5$ V, $V_{SS} = -5$ V, $V_S = \pm 3$ V, $I_S = 1$ mA
LEAKAGE CURRENTS					
Source Off Leakage, $I_{S(OFF)}$	$\pm 0.005$			nA typ	$V_{DD} = +5.5$ V, $V_{SS} = -5.5$ V
Source Off Leakage, $I_{S(OFF)}$	$\pm 0.2$		$\pm 5$	nA max	$V_D = \pm 4.5$ V, $V_S = \mp 4.5$ V; see Figure 21
Drain Off Leakage, $I_{D(OFF)}$	$\pm 0.005$		$\pm 5$	nA typ	$V_D = \pm 4.5$ V, $V_S = \mp 4.5$ V; see Figure 21
Drain Off Leakage, $I_{D(OFF)}$	$\pm 0.2$		$\pm 5$	nA max	$V_D = \pm 4.5$ V, $V_S = \mp 4.5$ V; see Figure 22
Channel On Leakage, $I_{D(ON)}$ , $I_{S(ON)}$	$\pm 0.005$		$\pm 5$	nA typ	$V_D = V_S = \pm 4.5$ V; see Figure 22
Channel On Leakage, $I_{D(ON)}$ , $I_{S(ON)}$	$\pm 0.2$		$\pm 5$	nA max	$V_D = V_S = \pm 4.5$ V; see Figure 23
DIGITAL INPUTS					
Input High Voltage, $V_{INH}$			2.4	V min	
Input Low Voltage, $V_{INL}$			0.8	V max	
Input Current, $I_{INL}$ or $I_{INH}$	0.005		$\pm 1$	$\mu\text{A}$ typ	$V_{IN} = V_{INL}$ or $V_{INH}$
Digital Input Capacitance, $C_{IN}$	2			$\mu\text{A}$ max	$V_{IN} = V_{INL}$ or $V_{INH}$
Digital Input Capacitance, $C_{IN}$				pF typ	
DYNAMIC CHARACTERISTICS <sup>1</sup>					
$t_{TRANSITION}$	60			ns typ	$R_L = 300 \Omega$ , $C_L = 35 \text{ pF}$ , $V_S = 3$ V; see Figure 24
$t_{ON}$ ( $\overline{EN}$ )	90	110	130	ns max	$R_L = 300 \Omega$ , $C_L = 35 \text{ pF}$ , $V_S = 3$ V; see Figure 24
$t_{ON}$ ( $\overline{EN}$ )	70			ns typ	$R_L = 300 \Omega$ , $C_L = 35 \text{ pF}$ , $V_S = 3$ V; see Figure 26
$t_{OFF}$ ( $\overline{EN}$ )	95	120	135	ns max	$R_L = 300 \Omega$ , $C_L = 35 \text{ pF}$ , $V_S = 3$ V; see Figure 26
$t_{OFF}$ ( $\overline{EN}$ )	25			ns typ	$R_L = 300 \Omega$ , $C_L = 35 \text{ pF}$ , $V_S = 3$ V; see Figure 26
$t_{OFF}$ ( $\overline{EN}$ )	40	45	50	ns max	$R_L = 300 \Omega$ , $C_L = 35 \text{ pF}$ , $V_S = 3$ V; see Figure 26
Break-Before-Make Time Delay, $t_{BBM}$	40			ns typ	$R_L = 300 \Omega$ , $C_L = 35 \text{ pF}$ , $V_{S1} = V_{S2} = 3$ V; see Figure 25
Break-Before-Make Time Delay, $t_{BBM}$			10	ns min	$R_L = 300 \Omega$ , $C_L = 35 \text{ pF}$ , $V_{S1} = V_{S2} = 3$ V; see Figure 25
Charge Injection	2			pC typ	$V_S = 0$ V, $R_S = 0$ $\Omega$ , $C_L = 1$ nF; see Figure 27
Charge Injection	4			pC max	$V_S = 0$ V, $R_S = 0$ $\Omega$ , $C_L = 1$ nF; see Figure 27
Off Isolation	-90			dB typ	$R_L = 50 \Omega$ , $C_L = 5$ pF, $f = 1$ MHz; see Figure 28
Total Harmonic Distortion, THD + N	0.025			% typ	$R_L = 600 \Omega$ , 2 V p-p, $f = 20$ Hz to 20 kHz
Channel-to-Channel Crosstalk	-90			dB typ	$R_L = 50 \Omega$ , $C_L = 5$ pF, $f = 1$ MHz; see Figure 30
-3 dB Bandwidth	580			MHz typ	$R_L = 50 \Omega$ , $C_L = 5$ pF; see Figure 29
$C_{S(OFF)}$	4			pF typ	$f = 1$ MHz
$C_{D(OFF)}$	7			pF typ	$f = 1$ MHz
$C_{D(ON)}$ , $C_{S(ON)}$	12			pF typ	$f = 1$ MHz
POWER REQUIREMENTS <sup>2</sup>					
$I_{DD}$	0.01		1	$\mu\text{A}$ typ	$V_{DD} = +5.5$ V, $V_{SS} = -5.5$ V
$I_{SS}$	0.01		1	$\mu\text{A}$ max	Digital inputs = 0 V or 5.5 V
$I_{SS}$				$\mu\text{A}$ typ	Digital inputs = 0 V or 5.5 V
$I_{SS}$				$\mu\text{A}$ max	Digital inputs = 0 V or 5.5 V

<sup>1</sup> Guaranteed by design; not subject to production test.

<sup>2</sup> The device is fully specified at a  $\pm 5$  V dual supply and at 5 V and 3.3 V single supplies. It is possible to operate the ADG633 with unbalanced supplies or at other voltage supplies ( $\pm 2$  V to  $\pm 6$  V, and 2 V to 12 V); however, the switch characteristics change. These changes include, but are not limited to: analog signal range, on resistance, leakage,  $V_{INL}$ ,  $V_{INH}$ , and switching times. The optimal power-up sequence for the device is: ground,  $V_{DD}$ ,  $V_{SS}$ , and then the digital inputs, before applying the analog input signal.

## SINGLE-SUPPLY OPERATION

$V_{DD} = 5$  V,  $V_{SS} = 0$  V, GND = 0 V,  $T_A = -40^\circ\text{C}$  to  $+125^\circ\text{C}$ , unless otherwise noted.

Table 2.

Parameter	+25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range				V	$V_{DD} = 4.5$ V, $V_{SS} = 0$ V
On Resistance, $R_{ON}$	85	160	200	$\Omega$ typ	$V_S = 0$ V to 4.5 V, $I_S = 1$ mA; see Figure 20
On-Resistance Match Between Channels, $\Delta R_{ON}$	4.5			$\Omega$ max	$V_S = 0$ V to 4.5 V, $I_S = 1$ mA; see Figure 20
On-Resistance Flatness, $R_{FLAT(ON)}$	8	9	10	$\Omega$ typ	$V_S = +3.5$ V, $I_S = 1$ mA
On-Resistance Flatness, $R_{FLAT(ON)}$	13	14	16	$\Omega$ max	$V_S = +3.5$ V, $I_S = 1$ mA
On-Resistance Flatness, $R_{FLAT(ON)}$				$\Omega$ typ	$V_{DD} = 5$ V, $V_{SS} = 0$ V, $V_S = 1.5$ V to 4 V, $I_S = 1$ mA
LEAKAGE CURRENTS					$V_{DD} = 5$ V
Source Off Leakage, $I_{S(OFF)}$	$\pm 0.005$			nA typ	$V_S = 1$ V/4.5 V, $V_D = 4.5$ V/1 V; see Figure 21
Source Off Leakage, $I_{S(OFF)}$	$\pm 0.2$		$\pm 5$	nA max	$V_S = 1$ V/4.5 V, $V_D = 4.5$ V/1 V; see Figure 21
Drain Off Leakage, $I_{D(OFF)}$	$\pm 0.005$		$\pm 5$	nA typ	$V_S = 1$ V/4.5 V, $V_D = 4.5$ V/1 V; see Figure 22
Drain Off Leakage, $I_{D(OFF)}$	$\pm 0.2$		$\pm 5$	nA max	$V_S = 1$ V/4.5 V, $V_D = 4.5$ V/1 V; see Figure 22
Channel On Leakage, $I_{D(ON)}$ , $I_{S(ON)}$	$\pm 0.005$		$\pm 5$	nA typ	$V_S = V_D = 1$ V or 4.5 V; see Figure 23
Channel On Leakage, $I_{D(ON)}$ , $I_{S(ON)}$	$\pm 0.2$		$\pm 5$	nA max	$V_S = V_D = 1$ V or 4.5 V; see Figure 23
DIGITAL INPUTS					
Input High Voltage, $V_{INH}$			2.4	V min	
Input Low Voltage, $V_{INL}$			0.8	V max	
Input Current, $I_{INL}$ or $I_{INH}$	0.005		$\pm 1$	$\mu\text{A}$ typ	$V_{IN} = V_{INL}$ or $V_{INH}$
Input Current, $I_{INL}$ or $I_{INH}$				$\mu\text{A}$ max	$V_{IN} = V_{INL}$ or $V_{INH}$
Digital Input Capacitance, $C_{IN}$	2			pF typ	
DYNAMIC CHARACTERISTICS <sup>1</sup>					
$t_{TRANSITION}$	100			ns typ	$R_L = 300$ $\Omega$ , $C_L = 35$ pF, $V_S = 3$ V; see Figure 24
$t_{ON}$ ( $\overline{EN}$ )	150	190	220	ns max	$R_L = 300$ $\Omega$ , $C_L = 35$ pF, $V_S = 3$ V; see Figure 24
$t_{ON}$ ( $\overline{EN}$ )	100			ns typ	$R_L = 300$ $\Omega$ , $C_L = 35$ pF, $V_S = 3$ V; see Figure 26
$t_{OFF}$ ( $\overline{EN}$ )	150	190	220	ns max	$R_L = 300$ $\Omega$ , $C_L = 35$ pF, $V_S = 3$ V; see Figure 26
$t_{OFF}$ ( $\overline{EN}$ )	25			ns typ	$R_L = 300$ $\Omega$ , $C_L = 35$ pF, $V_S = 3$ V; see Figure 26
Break-Before-Make Time Delay, $t_{BBM}$	35	45	50	ns max	$R_L = 300$ $\Omega$ , $C_L = 35$ pF, $V_S = 3$ V; see Figure 26
Break-Before-Make Time Delay, $t_{BBM}$	90		10	ns typ	$R_L = 300$ $\Omega$ , $C_L = 35$ pF, $V_S = 3$ V; see Figure 25
Break-Before-Make Time Delay, $t_{BBM}$				ns min	$R_L = 300$ $\Omega$ , $C_L = 35$ pF, $V_S = 3$ V; see Figure 25
Charge Injection	0.5			pC typ	$R_L = 300$ $\Omega$ , $C_L = 35$ pF, $V_{S1} = V_{S2} = 3$ V; see Figure 25
Charge Injection	1			pC max	$R_L = 300$ $\Omega$ , $C_L = 35$ pF, $V_{S1} = V_{S2} = 3$ V; see Figure 25
Off Isolation	-90			dB typ	$V_S = 2.5$ V, $R_S = 0$ $\Omega$ , $C_L = 1$ nF; see Figure 27
Channel-to-Channel Crosstalk	-90			dB typ	$V_S = 2.5$ V, $R_S = 0$ $\Omega$ , $C_L = 1$ nF; see Figure 27
-3 dB Bandwidth	520			MHz typ	$R_L = 50$ $\Omega$ , $C_L = 5$ pF, $f = 1$ MHz; see Figure 28
$C_{S(OFF)}$	5			pF typ	$R_L = 50$ $\Omega$ , $C_L = 5$ pF, $f = 1$ MHz; see Figure 30
$C_{D(OFF)}$	8			pF typ	$R_L = 50$ $\Omega$ , $C_L = 5$ pF; see Figure 29
$C_{D(ON)}$ , $C_{S(ON)}$	12			pF typ	$f = 1$ MHz
$C_{D(ON)}$ , $C_{S(ON)}$					$f = 1$ MHz
POWER REQUIREMENTS <sup>2</sup>					
$I_{DD}$	0.01		1	$\mu\text{A}$ typ	$V_{DD} = 5.5$ V
$I_{DD}$				$\mu\text{A}$ max	Digital inputs = 0 V or 5.5 V
$I_{DD}$					Digital inputs = 0 V or 5.5 V

<sup>1</sup> Guaranteed by design; not subject to production test.

<sup>2</sup> The device is fully specified at a  $\pm 5$  V dual supply and at 5 V and 3.3 V single supplies. It is possible to operate the ADG633 with unbalanced supplies or at other voltage supplies ( $\pm 2$  V to  $\pm 6$  V, and 2 V to 12 V); however, the switch characteristics change. These changes include, but are not limited to: analog signal range, on resistance, leakage,  $V_{INL}$ ,  $V_{INH}$ , and switching times. The optimal power-up sequence for the device is: ground,  $V_{DD}$ ,  $V_{SS}$ , and then the digital inputs, before applying the analog input signal.

$V_{DD} = 2.7$  V to  $3.6$  V,  $V_{SS} = 0$  V, GND = 0 V,  $T_A = -40^\circ\text{C}$  to  $+125^\circ\text{C}$ , unless otherwise noted.

Table 3.

Parameter	+25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range				V	$V_{DD} = 2.7$ V, $V_{SS} = 0$ V
On Resistance, $R_{ON}$	185 300	350	400	$\Omega$ typ $\Omega$ max $\Omega$ typ	$V_S = 0$ V to $2.7$ V, $I_S = 0.1$ mA; see Figure 20 $V_S = 0$ V to $2.7$ V, $I_S = 0.1$ mA; see Figure 20 $V_S = +1.5$ V, $I_S = 0.1$ mA
On-Resistance Match Between Channels, $\Delta R_{ON}$	2 4.5	6	7	$\Omega$ max	$V_S = +1.5$ V, $I_S = 0.1$ mA
LEAKAGE CURRENTS					$V_{DD} = 3.3$ V
Source Off Leakage, $I_{S(OFF)}$	$\pm 0.005$ $\pm 0.2$		$\pm 5$	nA typ nA max	$V_S = 1$ V/3 V, $V_D = 3$ V/1 V; see Figure 21 $V_S = 1$ V/3 V, $V_D = 3$ V/1 V; see Figure 21
Drain Off Leakage, $I_{D(OFF)}$	$\pm 0.005$ $\pm 0.2$		$\pm 5$	nA typ nA max	$V_S = 1$ V/3 V, $V_D = 3$ V/1 V; see Figure 22 $V_S = 1$ V/3 V, $V_D = 3$ V/1 V; see Figure 22
Channel On Leakage, $I_{D(ON)}$ , $I_{S(ON)}$	$\pm 0.005$ $\pm 0.2$		$\pm 5$	nA typ nA max	$V_S = V_D = 1$ V or $3$ V; see Figure 23 $V_S = V_D = 1$ V or $3$ V; see Figure 23
DIGITAL INPUTS					
Input High Voltage, $V_{INH}$			2.0	V min	
Input Low Voltage, $V_{INL}$			0.5	V max	
Input Current, $I_{INL}$ or $I_{INH}$	0.005		$\pm 1$	$\mu\text{A}$ typ $\mu\text{A}$ max	$V_{IN} = V_{INL}$ or $V_{INH}$ $V_{IN} = V_{INL}$ or $V_{INH}$
Digital Input Capacitance, $C_{IN}$	2			pF typ	
DYNAMIC CHARACTERISTICS <sup>1</sup>					
$t_{\text{TRANSITION}}$	170 300	370	400	ns typ ns max	$R_L = 300 \Omega$ , $C_L = 35$ pF, $V_S = 1.5$ V; see Figure 24 $R_L = 300 \Omega$ , $C_L = 35$ pF, $V_S = 1.5$ V; see Figure 24
$t_{ON}(\overline{EN})$	200 310	380	420	ns typ ns max	$R_L = 300 \Omega$ , $C_L = 35$ pF, $V_S = 1.5$ V; see Figure 26 $R_L = 300 \Omega$ , $C_L = 35$ pF, $V_S = 1.5$ V; see Figure 26
$t_{OFF}(\overline{EN})$	30 40	55	75	ns typ ns max	$R_L = 300 \Omega$ , $C_L = 35$ pF, $V_S = 1.5$ V; see Figure 26 $R_L = 300 \Omega$ , $C_L = 35$ pF, $V_S = 1.5$ V; see Figure 26
Break-Before-Make Time Delay, $t_{BBM}$	180		10	ns min	$R_L = 300 \Omega$ , $C_L = 35$ pF, $V_{S1} = V_{S2} = 1.5$ V; see Figure 25 $R_L = 300 \Omega$ , $C_L = 35$ pF, $V_{S1} = V_{S2} = 1.5$ V; see Figure 25
Charge Injection	1 2			pC typ pC max	$V_S = 1.5$ V, $R_S = 0$ $\Omega$ , $C_L = 1$ nF; see Figure 27 $V_S = 1.5$ V, $R_S = 0$ $\Omega$ , $C_L = 1$ nF; see Figure 27
Off Isolation	-90			dB typ	$R_L = 50 \Omega$ , $C_L = 5$ pF, $f = 1$ MHz; see Figure 28
Channel-to-Channel Crosstalk	-90			dB typ	$R_L = 50 \Omega$ , $C_L = 5$ pF, $f = 1$ MHz; see Figure 30
-3 dB Bandwidth	500			MHz typ	$R_L = 50 \Omega$ , $C_L = 5$ pF; see Figure 29
$C_{S(OFF)}$	5			pF typ	$f = 1$ MHz
$C_{D(OFF)}$	8			pF typ	$f = 1$ MHz
$C_{D(ON)}$ , $C_{S(ON)}$	12			pF typ	$f = 1$ MHz
POWER REQUIREMENTS <sup>2</sup>					
$I_{DD}$	0.01		1	$\mu\text{A}$ typ $\mu\text{A}$ max	$V_{DD} = 3.3$ V Digital inputs = 0 V or $3.3$ V Digital inputs = 0 V or $3.3$ V

<sup>1</sup> Guaranteed by design; not subject to production test.

<sup>2</sup> The device is fully specified at a  $\pm 5$  V dual supply and at 5 V and 3.3 V single supplies. It is possible to operate the ADG633 with unbalanced supplies or at other voltage supplies ( $\pm 2$  V to  $\pm 6$  V, and 2 V to 12 V); however, the switch characteristics change. These changes include, but are not limited to: analog signal range, on resistance, leakage,  $V_{INL}$ ,  $V_{INH}$ , and switching times. The optimal power-up sequence for the device is: ground,  $V_{DD}$ ,  $V_{SS}$ , and then the digital inputs, before applying the analog input signal.

## ABSOLUTE MAXIMUM RATINGS

T<sub>A</sub> = 25°C, unless otherwise noted.

Table 4.

Parameter	Rating
V <sub>DD</sub> to V <sub>SS</sub> <sup>1</sup>	13 V
V <sub>DD</sub> to GND	-0.3 V to +13 V
V <sub>SS</sub> to GND	+0.3 V to -6.5 V
Analog Inputs <sup>2</sup>	V <sub>SS</sub> – 0.3 V to V <sub>DD</sub> + 0.3 V
Digital Inputs <sup>2</sup>	GND – 0.3 V to V <sub>DD</sub> + 0.3 V or 10 mA, whichever occurs first
Peak Current, S or D	40 mA (pulsed at 1 ms, 10% duty cycle maximum)
Continuous Current, S or D	20 mA
Operating Temperature Range	-40°C to +125°C
Storage Temperature Range	-65°C to +150°C
Junction Temperature	150°C
θ <sub>JA</sub> Thermal Impedance	
16-Lead TSSOP	150.4°C/W
16-Lead LFCSP, 4-Layer Board	70°C/W
Lead Soldering	
Lead Temperature, Soldering (10 sec)	300°C
IR Reflow, Peak Temperature (<20 sec)	220°C
(Pb-Free) Soldering	
Reflow, Peak Temperature	260(+0/-5)°C
Time at Peak Temperature	20 sec to 40 sec
ESD	4 kV

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

Only one absolute maximum rating can be applied at any one time.

### ESD CAUTION



#### ESD (electrostatic discharge) sensitive device.

Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

<sup>1</sup> The device is fully specified at a ±5 V dual supply and at 5 V and 3.3 V single supplies. It is possible to operate the ADG633 with unbalanced supplies or at other voltage supplies (±2 V to ±6 V, and 2 V to 12 V); however, the switch characteristics change. These changes include, but are not limited to: analog signal range, on resistance, leakage, V<sub>INL</sub>, V<sub>INH</sub>, and switching times. The optimal power-up sequence for the device is: ground, V<sub>DD</sub>, V<sub>SS</sub>, and then the digital inputs, before applying the analog input signal.

<sup>2</sup> Overvoltages at Ax, EN, S, or D are clamped by internal diodes. Limit current to the maximum ratings given.

## PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

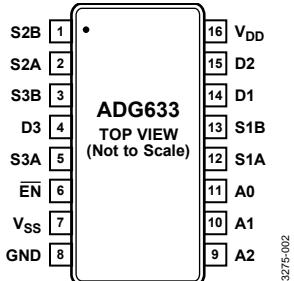
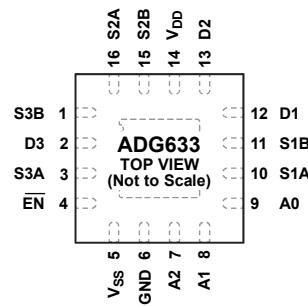


Figure 2. 16-Lead TSSOP Pin Configuration



NOTES  
1. THE EXPOSED PADDLE CAN BE LEFT FLOATING OR BE TIED TO V<sub>DD</sub>, V<sub>SS</sub>, OR GND.

03275-002

Figure 3. 16-Lead LFCSP Pin Configuration

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Table 5. Pin Function Descriptions

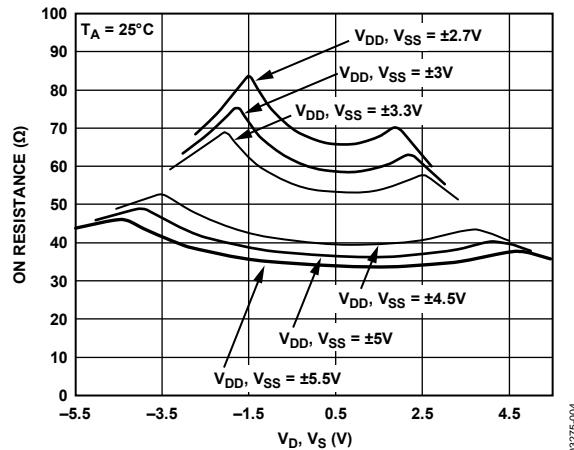
Pin No.		Mnemonic	Description
TSSOP	LFCSP		
1	15	S2B	Source Terminal of Multiplexer 2. Can be an input or output.
2	16	S2A	Source Terminal of Multiplexer 2. Can be an input or output.
3	1	S3B	Source Terminal of Multiplexer 3. Can be an input or output.
4	2	D3	Drain Terminal of Multiplexer 3. Can be an input or output.
5	3	S3A	Source Terminal of Multiplexer 3. Can be an input or output.
6	4	EN	Digital Control Input. Disables all multiplexers when set high.
7	5	V <sub>ss</sub>	Most Negative Power Supply Terminal. Tie this pin to GND when using the device with single-supply voltages.
8	6	GND	Ground (0 V) Reference.
9	7	A2	Digital Control Input.
10	8	A1	Digital Control Input.
11	9	A0	Digital Control Input.
12	10	S1A	Source Terminal of Multiplexer 1. Can be an input or output.
13	11	S1B	Source Terminal of Multiplexer 1. Can be an input or output.
14	12	D1	Drain Terminal of Multiplexer 1. Can be an input or output.
15	13	D2	Drain Terminal of Multiplexer 2. Can be an input or output.
16	14	V <sub>dd</sub>	Most Positive Power Supply Terminal.
Not applicable	EP	EP	Exposed Paddle. The exposed paddle can be left floating or be tied to V <sub>dd</sub> , V <sub>ss</sub> , or GND.

Table 6. ADG633 Truth Table

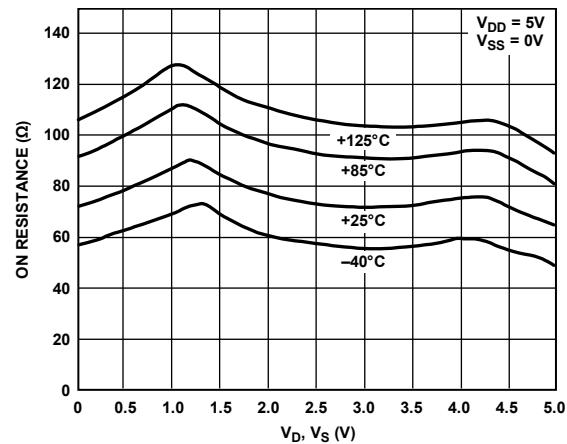
A2	A1	A0	EN	Switch Condition					
				Switch S1A/D1	Switch S1B/D1	Switch S2A/D2	Switch S2B/D2	Switch S3A/D3	Switch S3B/D3
X <sup>1</sup>	X <sup>1</sup>	X <sup>1</sup>	1	Off	Off	Off	Off	Off	Off
0	0	0	0	On	Off	On	Off	On	Off
0	0	1	0	Off	On	On	Off	On	Off
0	1	0	0	On	Off	Off	On	On	Off
0	1	1	0	Off	On	Off	On	On	Off
1	0	0	0	On	Off	On	Off	Off	On
1	0	1	0	Off	On	On	Off	Off	On
1	1	0	0	On	Off	Off	On	Off	On
1	1	1	0	Off	On	Off	On	Off	On

<sup>1</sup> X means the logic state does not matter; it can be either 0 or 1.

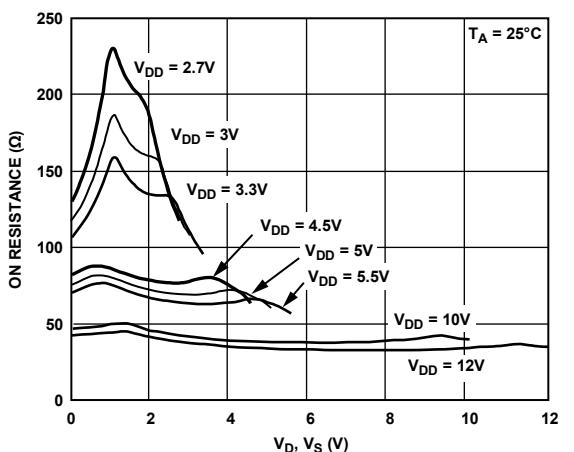
## TYPICAL PERFORMANCE CHARACTERISTICS



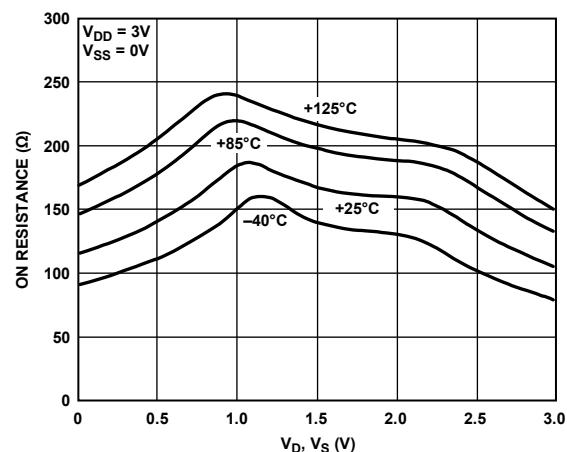
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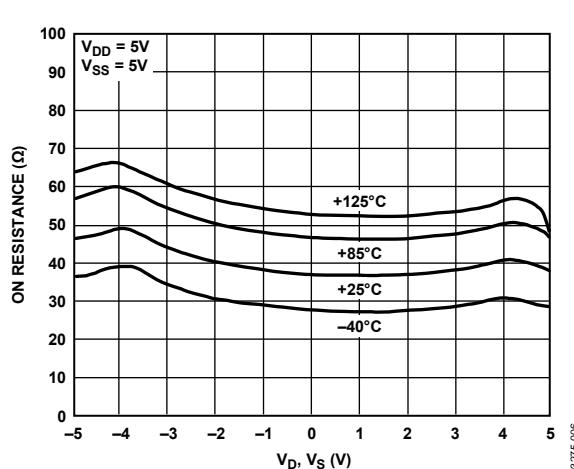
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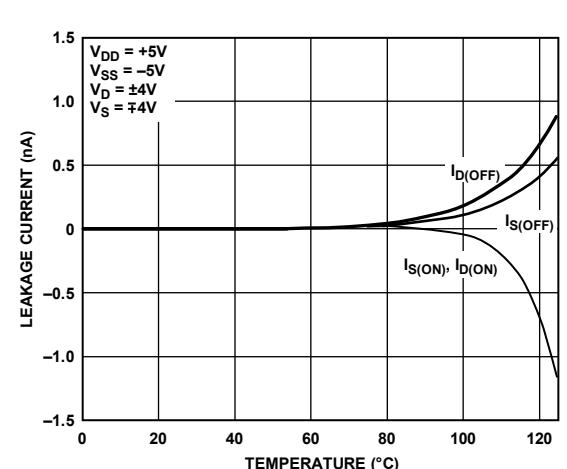
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03275-008



03275-006



03275-009

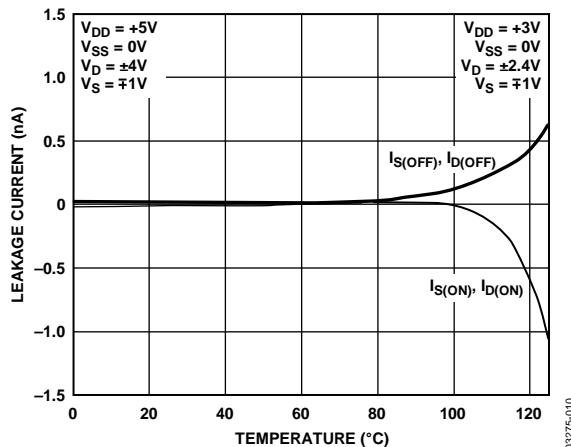


Figure 10. Leakage Current vs. Temperature, Single Supply

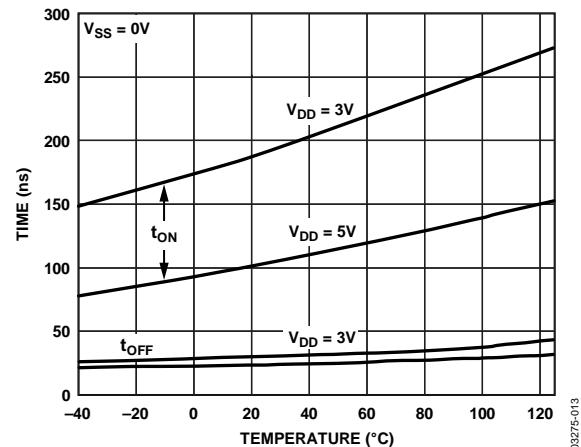
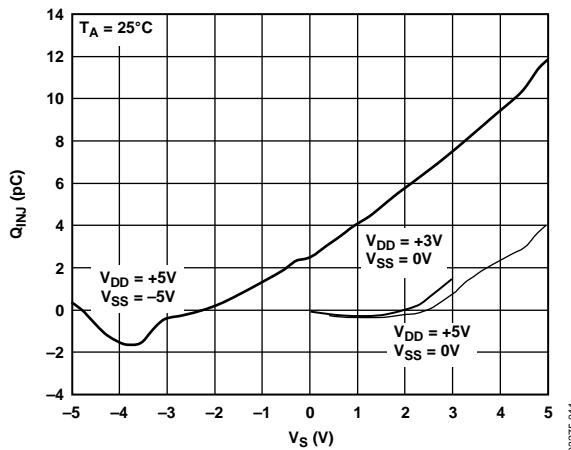
Figure 13.  $t_{ON}/t_{OFF}$  Times vs. Temperature, Single Supply

Figure 11. Charge Injection vs. Source Voltage

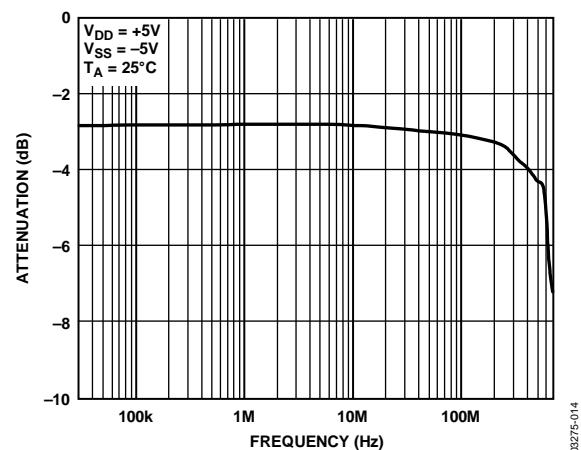


Figure 14. On Response vs. Frequency

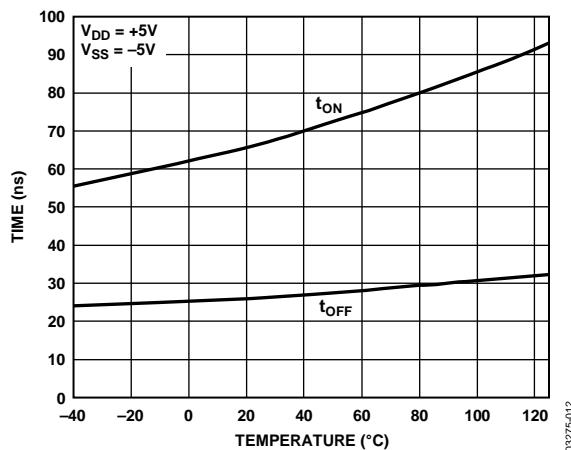
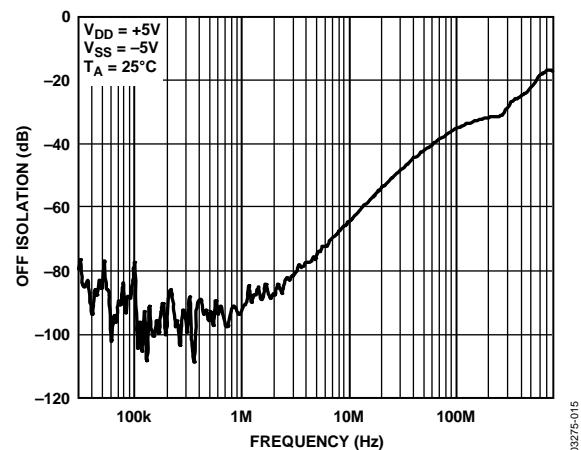
Figure 12.  $t_{ON}/t_{OFF}$  Times vs. Temperature, Dual Supplies

Figure 15. Off Isolation vs. Frequency

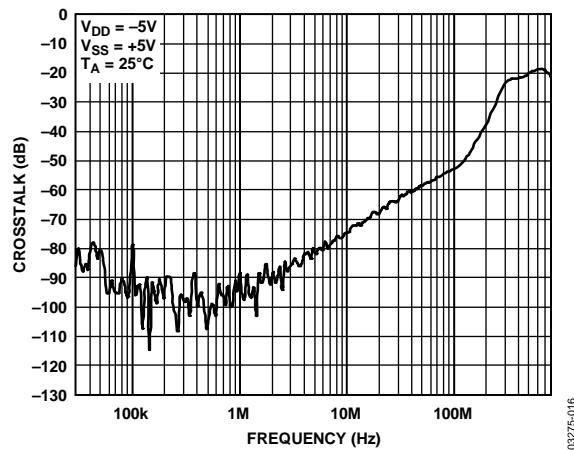


Figure 16. Crosstalk vs. Frequency

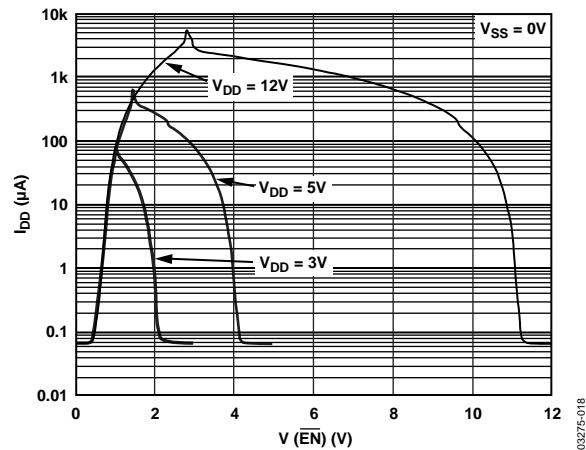
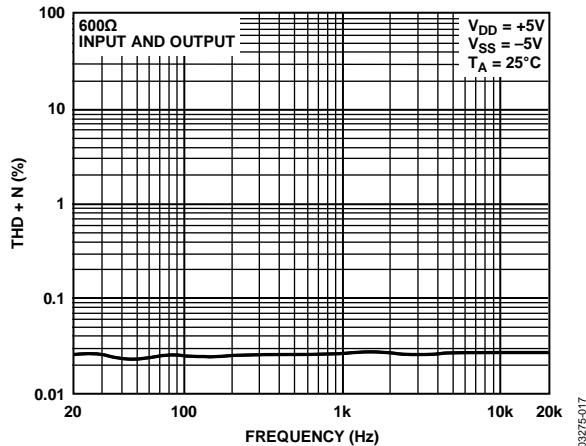
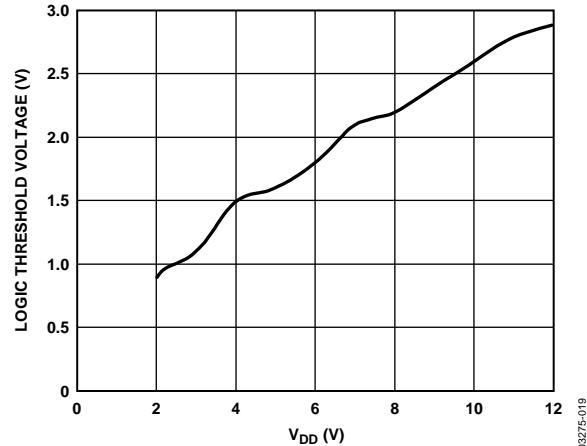
Figure 18.  $V_{DD}$  Current vs. Logic Level

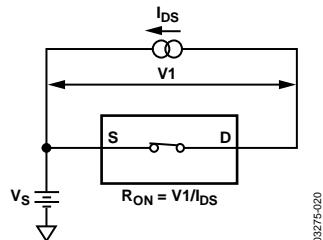
Figure 17. THD + Noise vs. Frequency

Figure 19. Logic Threshold Voltage vs.  $V_{DD}$

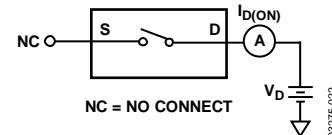
## TERMINOLOGY

<b>V<sub>DD</sub></b>	<b>V<sub>INH</sub></b>
Most positive power supply potential.	Minimum input voltage for Logic 1.
<b>V<sub>SS</sub></b>	<b>I<sub>INL</sub>, I<sub>INH</sub></b>
Most negative power supply potential.	Input current of the digital input.
<b>I<sub>DD</sub></b>	<b>C<sub>S(OFF)</sub></b>
Positive supply current.	Off switch source capacitance. Measured with reference to ground.
<b>I<sub>SS</sub></b>	<b>C<sub>D(OFF)</sub></b>
Negative supply current.	Off switch drain capacitance. Measured with reference to ground.
<b>GND</b>	<b>C<sub>D(ON)</sub>, C<sub>S(ON)</sub></b>
Ground (0 V) reference.	On switch capacitance. Measured with reference to ground.
<b>S</b>	<b>C<sub>IN</sub></b>
Source terminal. Can be an input or output.	Digital input capacitance.
<b>D</b>	<b>t<sub>ON</sub> (EN)</b>
Drain terminal. Can be an input or output.	Delay between applying the digital control input and the output switching on (see Figure 26).
<b>A<sub>x</sub></b>	<b>t<sub>OFF</sub> (EN)</b>
Logic control input.	Delay between applying the digital control input and the output switching off (see Figure 26).
<b>EN</b>	<b>t<sub>BBM</sub></b>
Active low digital input. When EN is high, the device is disabled and all switches are off. When EN is low, the Ax logic inputs determine the on switches.	On time, measured between 80% points of both switches when switching from one address state to another.
<b>V<sub>D</sub>, V<sub>S</sub></b>	<b>Charge Injection</b>
Analog voltage on Terminal D and Terminal S.	A measure of the glitch impulse transferred from the digital input to the analog output during switching.
<b>R<sub>ON</sub></b>	<b>Off Isolation</b>
Ohmic resistance between Terminal D and Terminal S.	A measure of unwanted signal coupling through an off switch.
<b>ΔR<sub>ON</sub></b>	<b>Crosstalk</b>
On-resistance match between any two channels, that is, $R_{ONMAX} - R_{ONMIN}$ .	A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.
<b>R<sub>FLAT(ON)</sub></b>	<b>Bandwidth</b>
Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range.	The frequency at which the output is attenuated by 3 dB.
<b>I<sub>S(OFF)</sub></b>	<b>On Response</b>
Source leakage current with the switch off.	The frequency response of the on switch.
<b>I<sub>D(OFF)</sub></b>	<b>Insertion Loss</b>
Drain leakage current with the switch off.	The loss due to the on resistance of the switch.
<b>I<sub>D(ON)</sub>, I<sub>S(ON)</sub></b>	
Channel leakage current with the switch on.	
<b>V<sub>INL</sub></b>	
Maximum input voltage for Logic 0.	

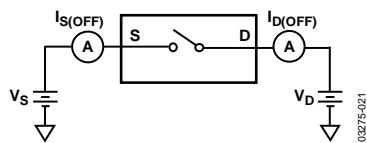
## TEST CIRCUITS



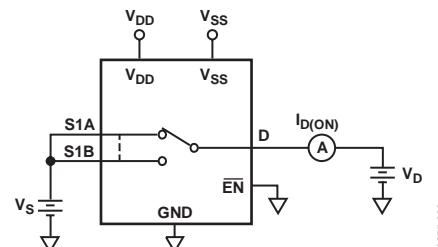
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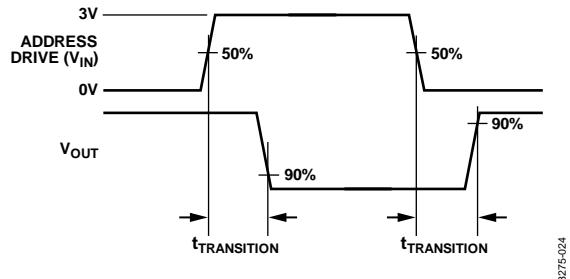
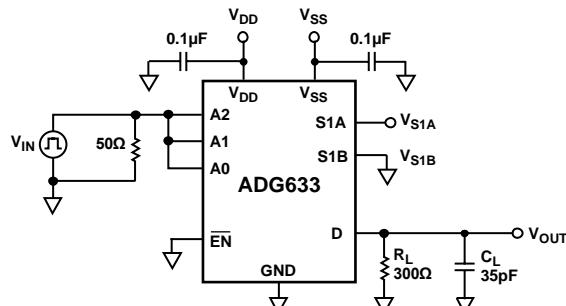
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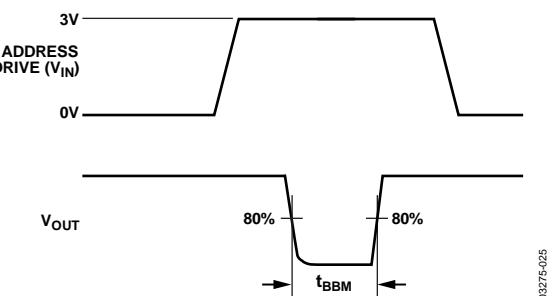
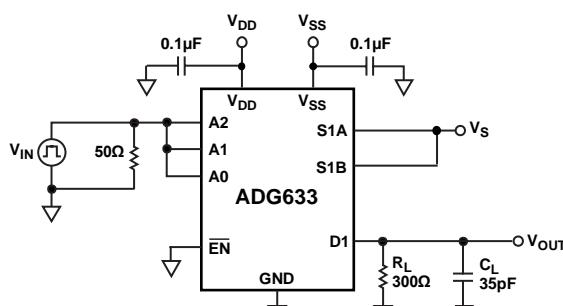
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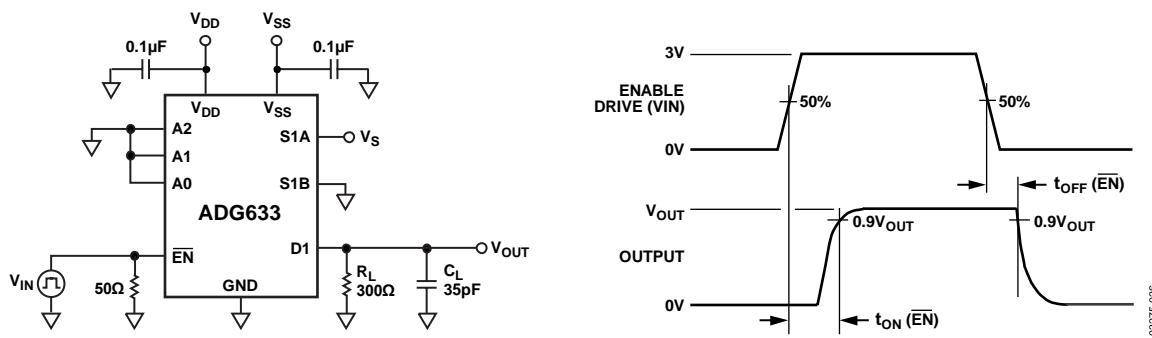
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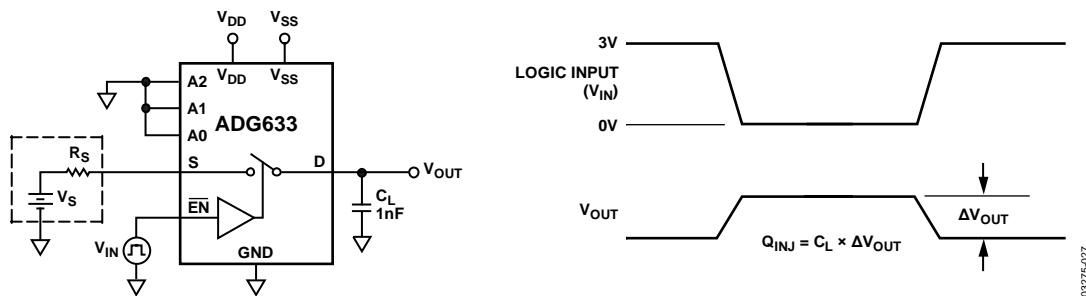
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Figure 26. Enable Delay,  $t_{ON}(EN)$ ,  $t_{OFF}(EN)$ 

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03275-027

Figure 27. Charge Injection

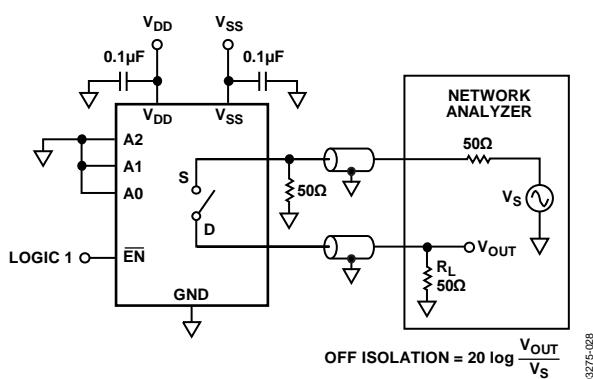


Figure 28. Off Isolation

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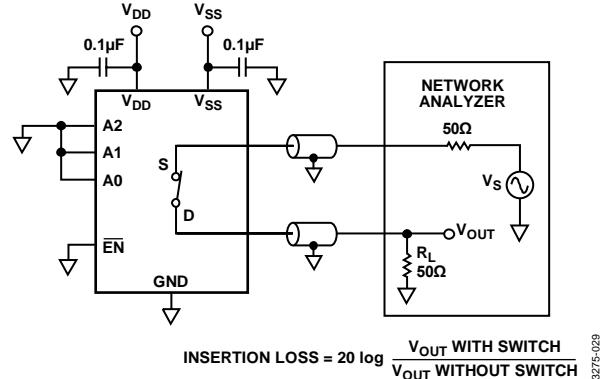


Figure 29. Bandwidth

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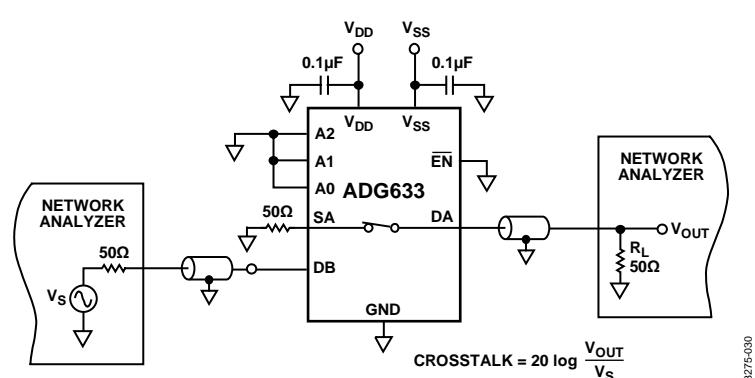


Figure 30. Channel-to-Channel Crosstalk

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## OUTLINE DIMENSIONS

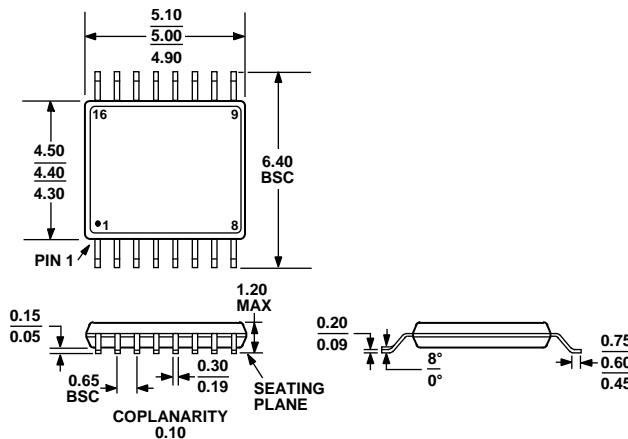


Figure 31. 16-Lead Thin Shrink Small Outline Package [TSSOP]  
(RU-16)  
Dimensions shown in millimeters

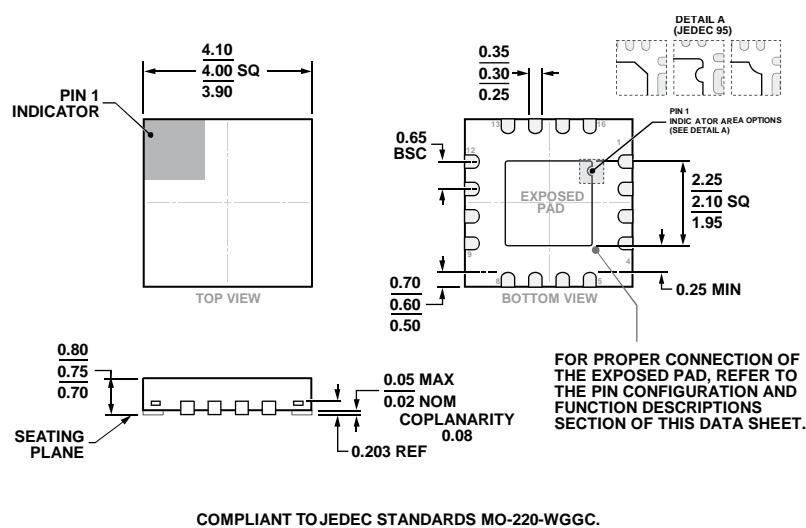


Figure 32. 16-Lead Lead Frame Chip Scale Package [LFCSP]  
4 mm × 4 mm Body and 0.75 mm Package Height  
(CP-16-23)  
Dimensions shown in millimeters

## ORDERING GUIDE

Model <sup>1</sup>	Temperature Range	Package Description	Package Option
ADG633YRU	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG633YRU-REEL7	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG633YRUZ	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG633YRUZ-REEL7	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG633YCPZ	-40°C to +85°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16-23
ADG633YCPZ-REEL7	-40°C to +85°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16-23

<sup>1</sup> Z = RoHS Compliant Part.

**NOTES**

**NOTES**